

Enhanced ultrafast power diode

Rev.03 - 22 November 2017

Product data sheet

# 1. General description

Enhanced ultrafast power diode in a TO252 (DPAK) surface-mountable plastic package.

### 2. Features and benefits

- High thermal cycling performance
- Low on-state losses
- Low thermal resistance
- Soft recovery characteristic
- Surface-mountable package

## 3. Applications

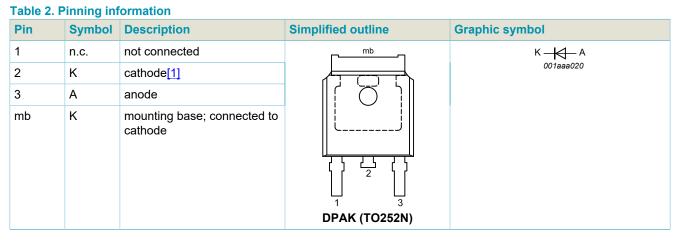
- Dual mode (DCM and CCM) Power Factor Correction (PFC)
- Power Factor Correction (PFC) for Interleaved Topology
- U-inverter (DC-AC converter for individual solar panels)

## 4. Quick reference data

Table	1.	Quick	reference	data
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Symbol	Parameter	Conditions	Mir	і Тур	Max	Unit
V <sub>R</sub>	reverse voltage	DC	-	-	600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; T <sub>mb</sub> ≤ 115 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	-	9	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 115 °C; square-wave pulse	-	-	18	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	-	-	91	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	-	-	100	A
Static chara	octeristics					,
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	1.45	1.9	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C	-	1.25	1.7	V
Dynamic ch	aracteristics		· ·			
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	17.5	35	ns

### 5. Pinning information



[1] It is not possible to connect to pin 2 of the SOT428 package.

# 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BYV29FD-600	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	TO252N				

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### 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	600	V
V <sub>RWM</sub>	crest working reverse voltage		-	600	V
V <sub>R</sub>	reverse voltage	DC	-	600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ;T <sub>mb</sub> ≤ 115 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	9	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 115 °C; square-wave pulse	-	18	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	-	91	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	-	100	A
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

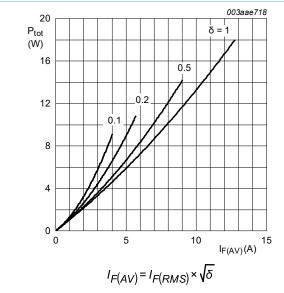


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

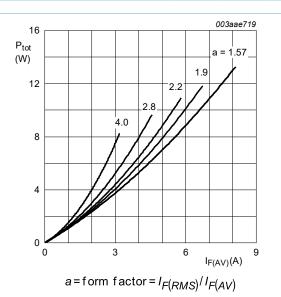
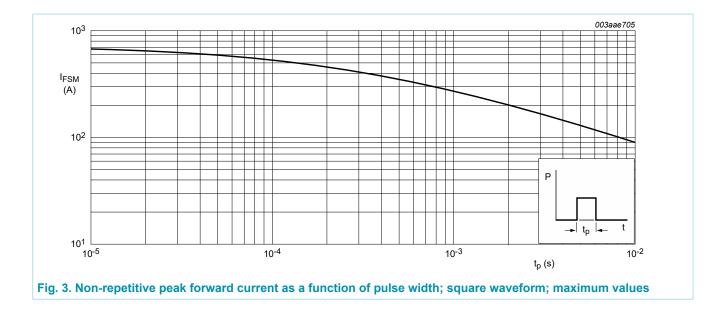


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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# BYV29FD-600

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### 8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. <u>4</u>	-	-	2.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

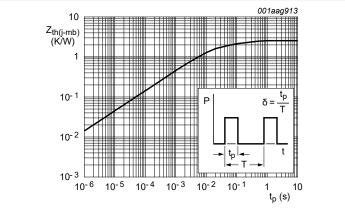
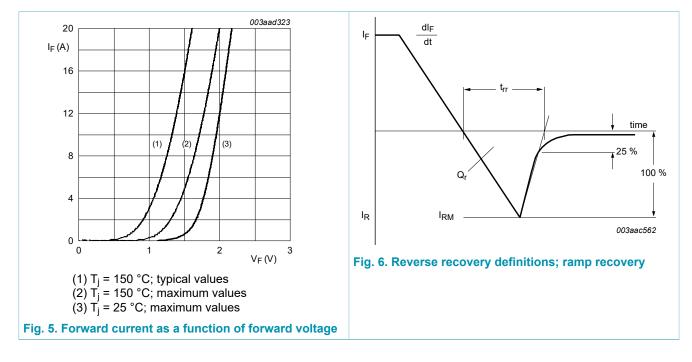


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse width

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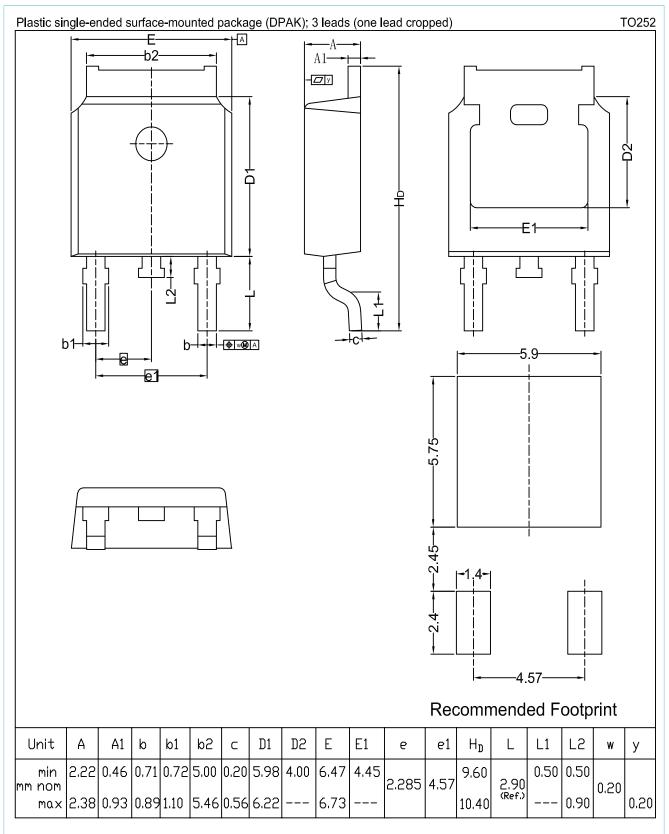
### 9. Characteristics

Table 6. Cha	aracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·				
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	1.45	1.9	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C	-	1.25	1.7	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 100 °C	-	-	1.5	mA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	50	μA
Dynamic cl	haracteristics	· · · · · · · · · · · · · · · · · · ·	·			
t <sub>rr</sub>	reverse recovery time	$I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 100 A/µs; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	17.5	35	ns
I <sub>RM</sub>	peak reverse recovery current	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; <u>Fig. 6</u>	-	1.5	-	A
Q <sub>r</sub>	recovered charge		-	13	-	nC
$V_{FR}$	forward recovery voltage	I <sub>F</sub> = 1 A; dI <sub>F</sub> /dt = 100 A/μs; <u>Fig. 6</u>	-	3.2	-	V



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### 10. Package outline



#### Fig. 7. Package outline DPAK (TO252N)

BYV29FD-600

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# 11. Revision history

Table 6. Revision hist	ory	
Document ID	Date	Changes
BYV29FD-600 Rev.01	20110307	Initial release
BYV29FD-600 Rev.02	20170815	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of WeEn Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Update "Package outline" due to subcon transfer.</li> </ul>
BYV29FD-600 Rev.03	20171122	<ul> <li>Add version number and revision history on this datasheet.</li> <li>Update "SOT428" to "TO252" on "General description" section.</li> </ul>

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## 12. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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